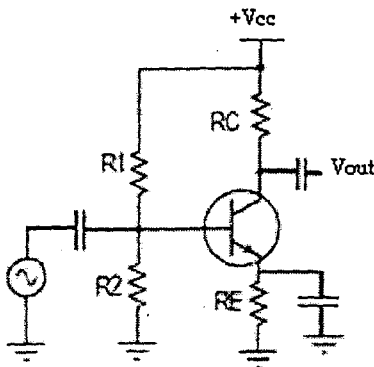


Answer Question No.8 and any Four from the rest

1. (a) How does the free electron concentration increase over the intrinsic value in an n-type semiconductor? Will the hole concentration remain constant at the intrinsic value? If not, why?  
(b) For what voltage will the reverse current in a p-n junction Ge diode reach 90% of its saturation value at room temperature? What is the ratio of the current for a forward bias of 0.05 V to the current for the same magnitude of reverse-bias.  
(c) How does the position of Fermi level modify with the temperature? Explain in brief. 5+6+4
2. (a) What are the factors on which intrinsic carrier concentrations of semiconductor depend?  
(b) Discuss the operation of a full wave bridge rectifier with resistive load. Discuss the role of filters  
(c) Determine the maximum and minimum values of Zener current if it is used in a voltage regulator circuit where the load resistance  $R_L=5\text{ K}\Omega$ ,  $R_S=10\text{ K}\Omega$ , Zener voltage  $V_Z=30\text{V}$  and the unregulated supply voltage varies between 100V and 120V. 4+6+5
3. (a) In the saturation region of BJT, what exactly saturates?  
(b) Why in BJT base region is made thinner and is most lightly doped (compared to emitter and collector)?  
(c) In a transistor CE configuration the voltage across  $5\text{K}\Omega$  load resistance is 5V, determine the collector current, base current and emitter current if  $\alpha = 0.96$ . 4+5+6
4. (a) Define thermal runaway and stability factor of BJT.  
(b) What are the disadvantages of "Collector to Base Bias Scheme".  
(c) In the given circuit  $I_E=2\text{ mA}$ ,  $I_B=50\text{ }\mu\text{A}$ ,  $V_{BE}=0.2\text{V}$ ,  $R_E=1\text{K}\Omega$ ,  $R_2=10\text{ K}\Omega$ ,  $V_{CC}=10\text{V}$ , find the value of  $R_1$ ?



5. a) Establish the relation between  $\alpha$  and  $\beta$  of BJT.  
b) Discuss the difference between positive and negative feedback  
c) Discuss the current voltage characteristics of JFET.

4+5+6

6. (a) State and prove De-Morgan's law of Boolean algebra.  
(b) Realize a AND gate using NOR gate only.  
(c) Prove that  $A + \bar{A}B = A + B$

6+4+5

7. (a) An inverting amplifier (OP-AMP) with input voltage is 1 V , input resistance is  $1K\Omega$ , and feedback resistance  $5K\Omega$ , find output voltage and voltage gain of the amplifier.  
(b) Discuss the operation of OPAMP based (i) Integrator (ii) Subtractor (iii) Non-inverting Amplifiers.  
(c) What do you mean by "virtual grounding"?

5+6+4

8. Answer the followings (any two)
- Discuss the consequences of 'Early effect'.
  - What are the differences between an un-doped and an equally doped semiconductor?
  - Can transistor action be realized by connecting two back-to-back diodes? If not, explain the reason?
  - Discuss the operation of positive Clipper circuit.

5x2